

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	75mΩ @ V _{GS} = -4.5V	-3.8A
	137mΩ @ V _{GS} = -2.5V	-3.0A

Description

This MOSFET is designed to minimize on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

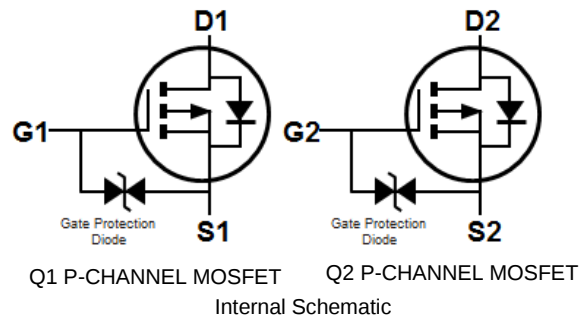
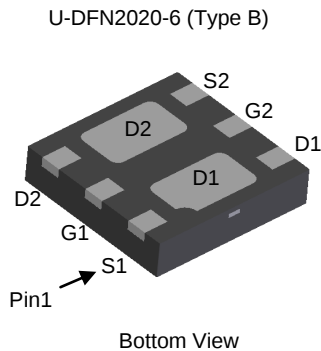
- Load Switch
- Power Management Functions
- Portable Power Adaptors

Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

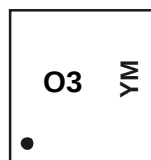

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2075UFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2075UFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

U-DFN2020-6 (Type B)



O3 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: F = 2018)
 M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.8 -3.0	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-1.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-25	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-13	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	8.5	mJ

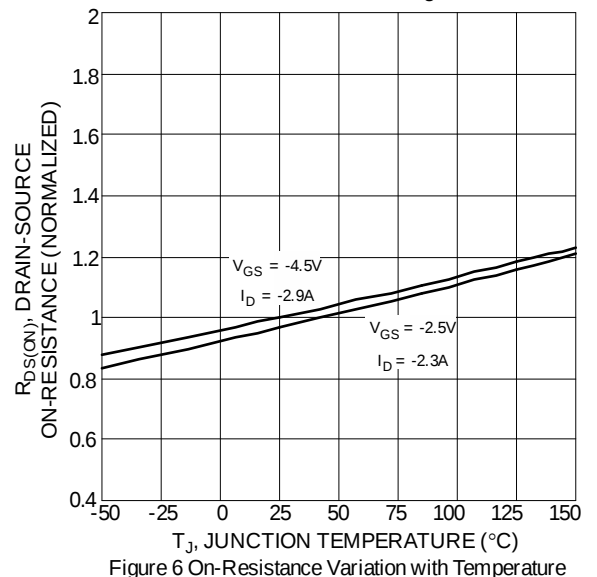
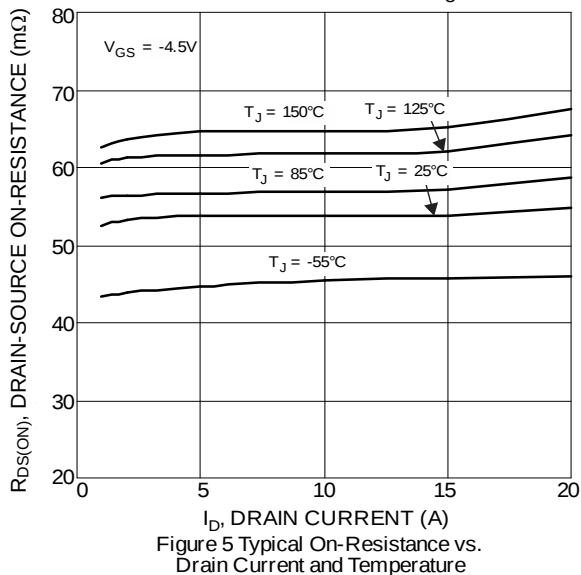
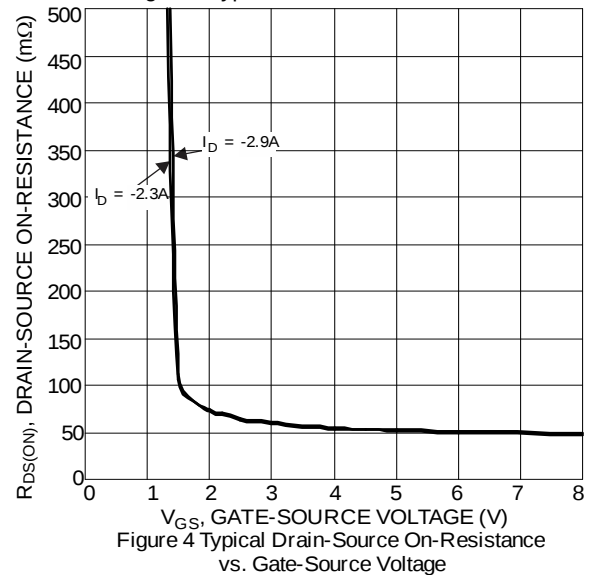
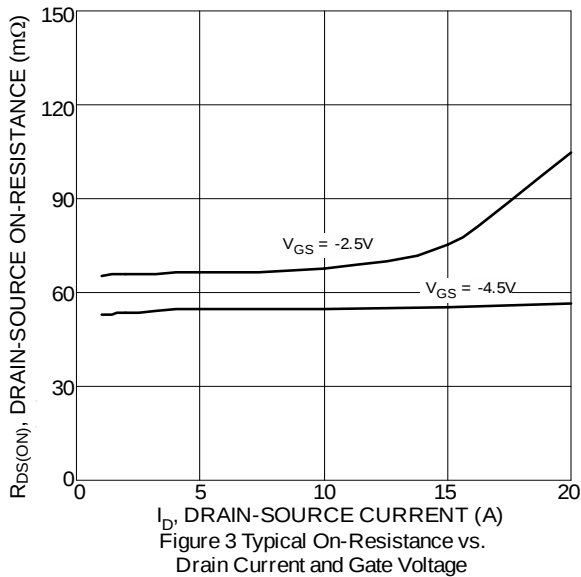
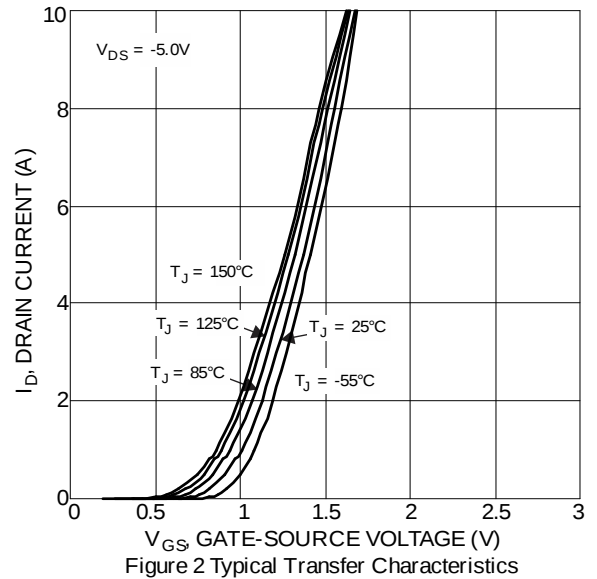
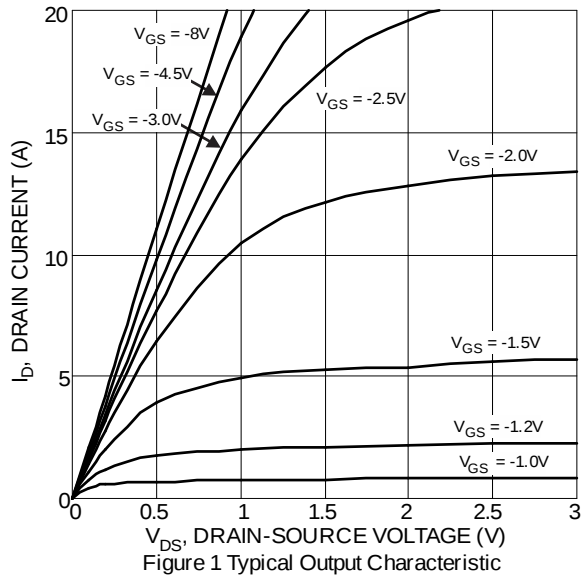
Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	178	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	92	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	22	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±6.4V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.35	—	-1.4	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	53	75	mΩ	V _{GS} = -4.5V, I _D = -2.9A
		—	64	137		V _{GS} = -2.5V, I _D = -2.3A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -3.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	642	—	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	98	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	87	—	pF	
Gate Resistance	R _g	—	26.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	8.8	—	nC	V _{DS} = -10V, I _D = -3.7A
Total Gate Charge (V _{GS} = -8V)		—	15	—	nC	
Gate-Source Charge	Q _{gs}	—	0.9	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.5	—	ns	V _{DD} = -10V, V _{GS} = -4.5V, R _L = 3.3Ω, R _g = 1Ω
Turn-On Rise Time	t _r	—	22.6	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	34.1	—	ns	
Turn-Off Fall Time	t _f	—	34.3	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	13	—	ns	I _S = -3.0A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	3.3	—	nC	I _S = -3.0A, dI/dt = 100A/μs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided
 - Device mounted on on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



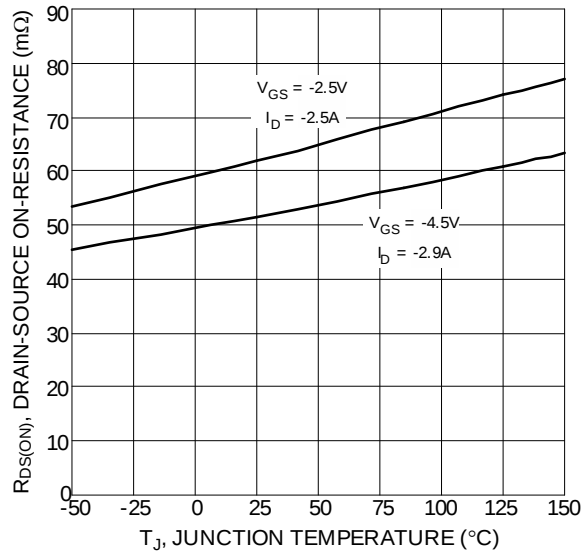


Figure 7 On-Resistance Variation with Temperature

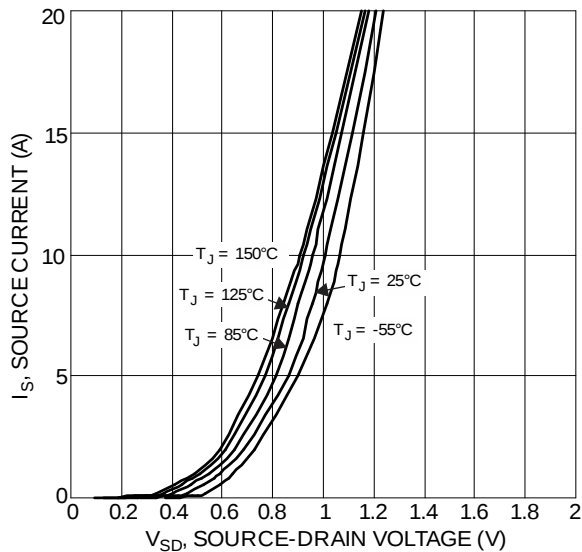


Figure 9 Diode Forward Voltage vs. Current

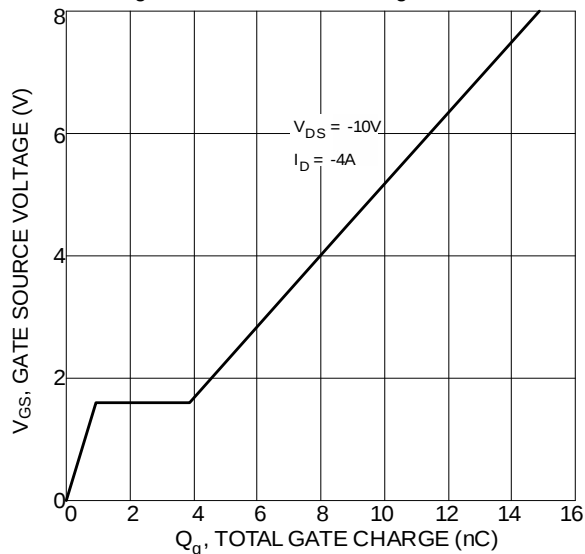


Figure 11 Gate Charge

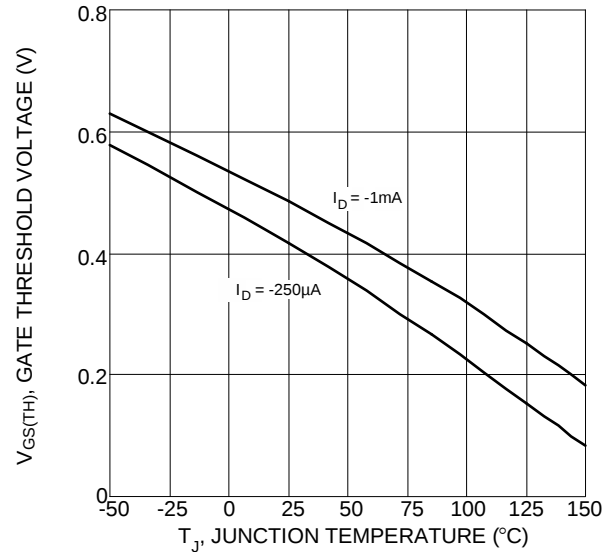


Figure 8 Gate Threshold Variation vs. Junction Temperature

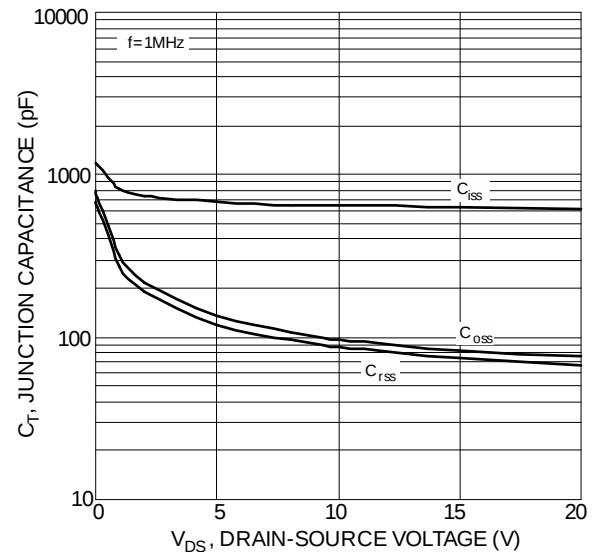


Figure 10 Typical Junction Capacitance

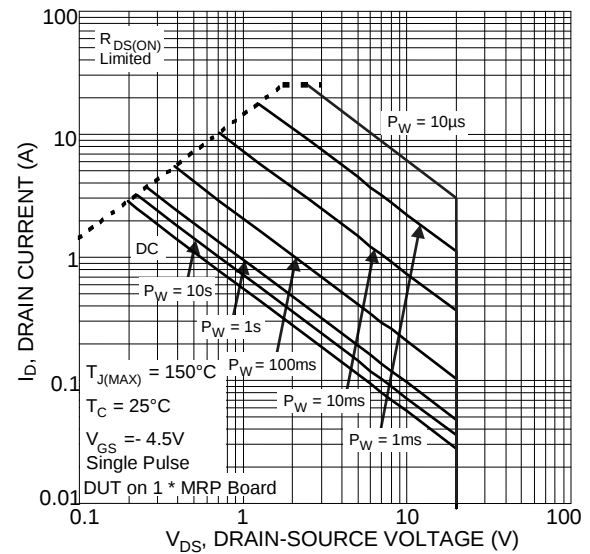
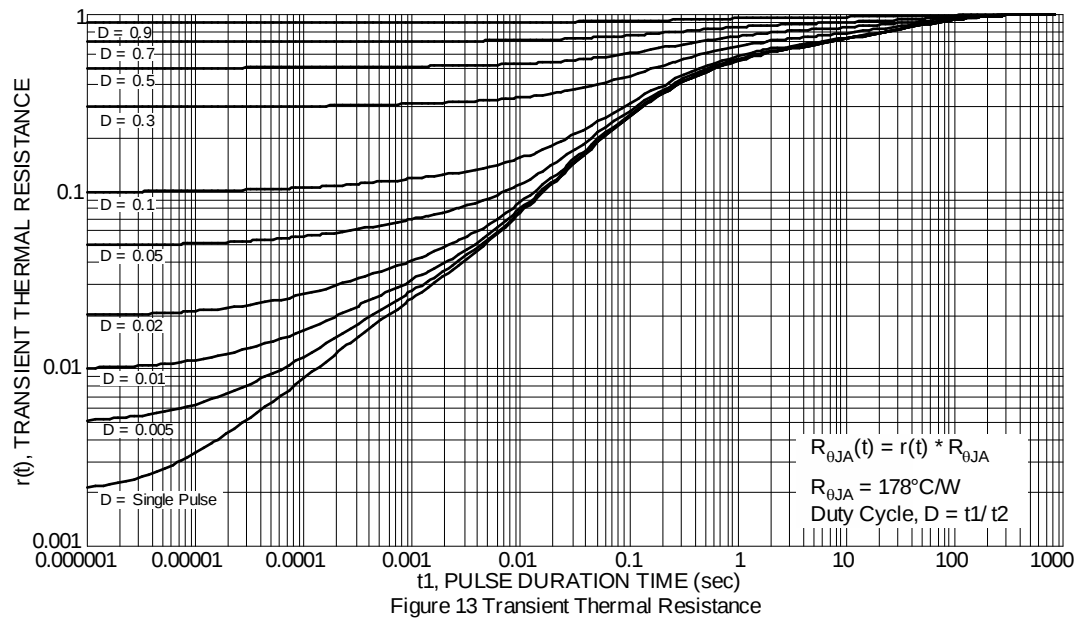


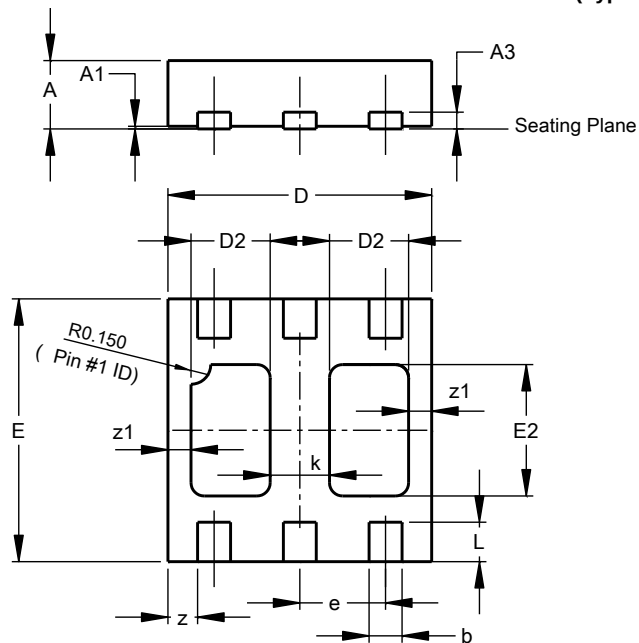
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)

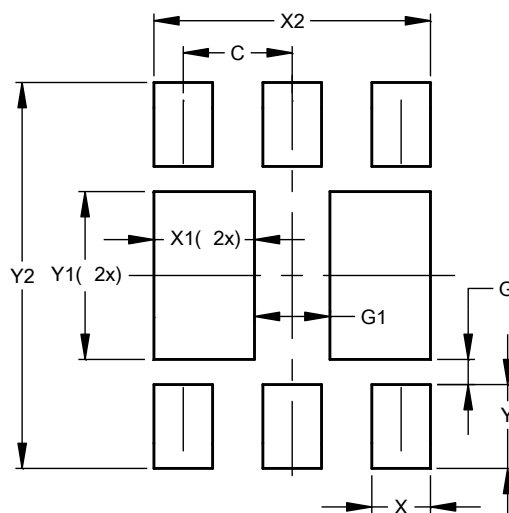


U-DFN2020-6 (Type B)			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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